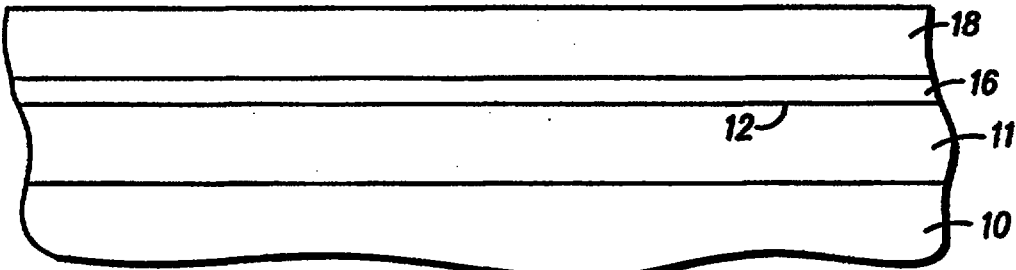




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(54) Title: LOW RESISTANCE MAGNETIC TUNNELING JUNCTION  (57) Abstract A low resistance magnetic tunnel junction with low resistance barrier layer and method of fabrication is disclosed. A first magnetic layer of material with a surface is provided and a continuous layer of material, e.g. aluminum, is formed on the surface of the first magnetic layer. The continuous layer of material is treated to produce a low resistance barrier layer of oxynitride material and a second magnetic layer is formed on the barrier layer of oxynitride material to complete the low resistance magnetic tunnel junction.		